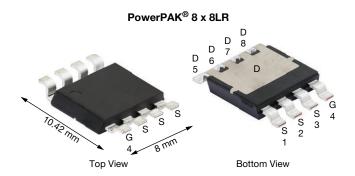
Vishay Siliconix

Automotive P-Channel 40 V (D-S) 175 °C MOSFET



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- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Thin 1.6 mm package
- Very low thermal resistance
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



PRODUCT SUMMARY				
V _{DS} (V)	-40			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.0020			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.0029			
I _D (A) ^e	-230			
Configuration	Single			

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D P-Channel MOSFET

ORDERING INFORMATION				
Package	PowerPAK® 8 x 8LR			
Lead (Pb)-free and halogen-free	SQJQ141ELR (for detailed order number please see www.vishay.com/doc?79776)			

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage	V_{DS}	-40			
Gate-source voltage		V_{GS}	± 20	V	
Continuous drain current ^e Continuous source current (diode conduction)	T _C = 25 °C	- I _D	-230		
	T _C = 125 °C		-133		
Continuous source current (diode conduction) e		I _S	-194	А	
Pulsed drain current a, e		I _{DM}	-910		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	-66		
Single pulse avalanche energy	L = U.T IIII	E _{AS}	218	mJ	
Maximum power dissipation ^e	T _C = 25 °C	Б	214	\\\	
	T _C = 125 °C	P_{D}	71	W	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C	
Soldering recommendations (peak temperature) ^c		-	260	7	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient PC	B mount b	R_{thJA}	44	°C/W	
Junction-to-case (drain) ^d		R_{thJC}	0.7	C/VV	

Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- b. When mounted on 1" square PCB (FR4 material)
- c. See solder profile (www.vishay.com/doc?73257). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- d. As per JESD51-14
- e. Values based on RthJC and TC of 25 °C. Actual values achievable will be dependent on the thermal characteristics of the complete system

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0$, $I_D = -250 \mu A$		-40	-	-	V
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$		-1.5	-2	-2.5	
Gate-source leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = -40 V	-	-	-1	
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = -40 V, T _J = 125 °C	-	-	-200	μA
		V _{GS} = 0 V	V _{DS} = -40 V, T _J = 175 °C	-	-	-500	
On-state drain current ^a	I _{D(on)}	V _{GS} = -10 V	$V_{DS} \ge -5 \text{ V}$	-100	-	=.	Α
		V _{GS} = -4.5 V	I _D = -8 A	-	0.0020	0.0029	Ω
Drain-source on-state resistance ^a	l p	V _{GS} = -10 V	I _D = -10 A	-	0.0014	0.0020	
	R _{DS(on)}	V _{GS} = -10 V	I _D = -10 A, T _J = 125 °C	-	-	0.0035	
		V _{GS} = -10 V	I _D = -10 A, T _J = 175 °C	=	-	0.0040	
Forward transconductance b	9fs	V _{DS} =	= -15 V, I _D = -50 A	-	180	=.	S
Dynamic ^b							
Input capacitance	C _{iss}			-	23 979	33 571	
Output capacitance	Coss	$V_{GS} = 0 V$	V _{DS} = -25 V, f = 1 MHz	-	1640	2296	pF
Reverse transfer capacitance	C _{rss}			-	1478	2082	
Total gate charge ^c	Qg			1	497	746	
Gate-source charge ^c	Q _{gs}	$V_{GS} = 10 \text{ V}$	V _{DS} = -20 V, I _D = -30 A	-	95	-	nC
Gate-drain charge ^c	Q _{gd}			-	84	-	
Gate resistance	R _g	f = 1 MHz		0.8	2.2	3.3	Ω
Turn-on delay time ^c	t _{d(on)}			-	19	29	
Rise time ^c	t _r		$R_L = 0.67 \Omega$	-	21	45	
Turn-off delay time ^c	t _{d(off)}	$I_D\cong$ -30 A, $V_{GEN}=$ -10 V, $R_g=$ 1 Ω		-	234	351	ns -
Fall time ^c	t _f			-	85	128	
Source-Drain Diode Ratings and Cha	aracteristics ^b						
	ta	I _{FM} = -20 A, di/dt = 100 A/μs		-	24	-	
Reverse recovery time	t _b			-	24	-	ns
	t _{rr}			-	48	96	
Reverse recovery charge	Q _{rr}			-	54	108	nC
Reverse recovery current	I _{RM}			-	-	-2.0	Α
Pulsed current ^a	I _{SM}			-	-	-776	Α
Forward voltage	V _{SD}	I _F = -50 A, V _{GS} = 0		-	-0.8	-1.1	V

Notes

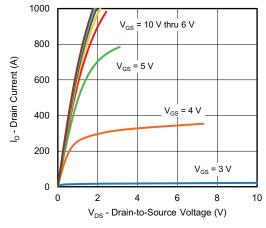
- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

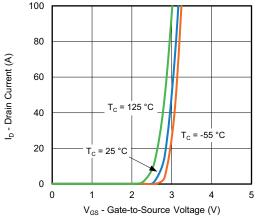
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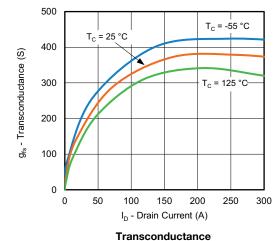
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Output Characteristics



Transfer Characteristics



500 400 (Y) tu au 300 Single 200 - T_c = 25 °C - T_c = 25 °C - T_c = 125 °C - T_c = 12

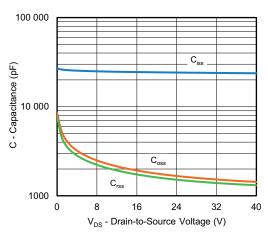
V_{GS} - Gate-to-Source Voltage (V) **Transfer Characteristics**

 $T_C = -55$ °C

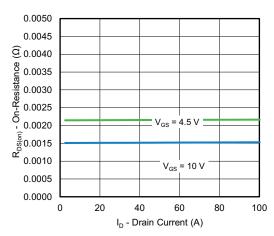
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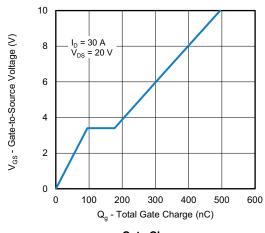
Capacitance



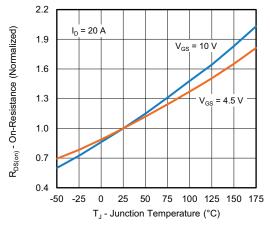
On-Resistance vs. Drain Current



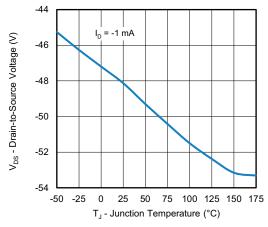
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



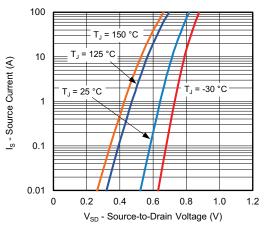




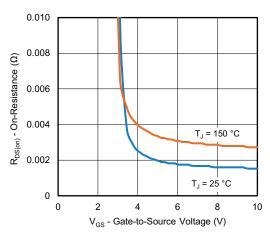
On-Resistance vs. Junction Temperature



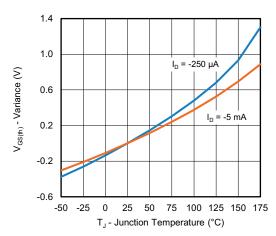
Drain Source Breakdown vs. Junction Temperature



Source Drain Diode Forward Voltage

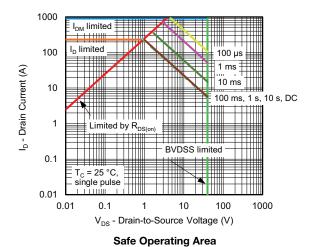


On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



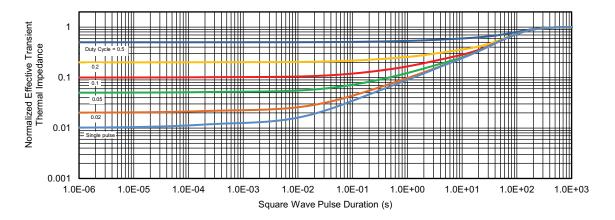


Note

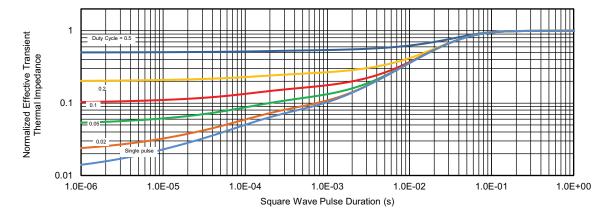
a. $V_{GS} > \mbox{minimum} \ V_{GS}$ at which $R_{DS(on)}$ is specified



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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